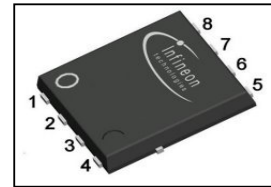


**OptiMOS™3 Power-Transistor**
**Features**

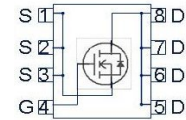
- Optimized for dc-dc conversion
- N-channel, normal level
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Low on-resistance  $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC<sup>1)</sup> for target application
- Halogen-free according to IEC61249-2-21


**Product Summary**

$V_{DS}$	200	V
$R_{DS(on),max}$	90	mΩ
$I_D$	15.2	A

**PG-TDSON-8**


Type	Package	Marking
BSC900N20NS3 G	PG-TDSON-8	900N20NS


**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	$I_D$	$T_C=25\text{ °C}$	15.2	A
		$T_C=100\text{ °C}$	10.7	
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	$T_C=25\text{ °C}$	61	
Avalanche energy, single pulse	$E_{AS}$	$I_D=7.6\text{ A}$ , $R_{GS}=25\text{ }\Omega$	100	mJ
Reverse diode $dv/dt$	$dv/dt$		10	kV/ $\mu$ s
Gate source voltage	$V_{GS}$		$\pm 20$	V
Power dissipation	$P_{tot}$	$T_C=25\text{ °C}$	62.5	W
Operating and storage temperature	$T_j$ , $T_{stg}$		-55 ... 150	°C
IEC climatic category; DIN IEC 68-1			55/150/56	

<sup>1)</sup>J-STD20 and JESD22

<sup>2)</sup> see figure 3

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Thermal characteristics**

Thermal resistance, junction - case	$R_{thJC}$		-	-	2	K/W
Thermal resistance, junction - ambient	$R_{thJA}$	6 cm <sup>2</sup> cooling area <sup>3)</sup>	-	-	50	

**Electrical characteristics, at  $T_j=25\text{ }^\circ\text{C}$ , unless otherwise specified**
**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$	200	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_D=30\text{ }\mu\text{A}$	2	3	4	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=160\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ }^\circ\text{C}$	-	0.1	1	$\mu\text{A}$
		$V_{DS}=160\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=125\text{ }^\circ\text{C}$	-	10	100	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$	-	1	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}$ , $I_D=7.6\text{ A}$	-	77	90	m $\Omega$
Gate resistance	$R_G$		-	2.2	-	$\Omega$
Transconductance	$g_{fs}$	$ V_{DS} >2 I_D R_{DS(on)max}$ , $I_D=7.6\text{ A}$	8	16	-	S

<sup>3)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical in still air.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics**

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=100\text{ V},$ $f=1\text{ MHz}$	-	690	920	pF
Output capacitance	$C_{oss}$		-	52	69	
Reverse transfer capacitance	$C_{rss}$		-	5.2	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=100\text{ V},$ $V_{GS}=10\text{ V}, I_D=7.6\text{ A},$ $R_G=1.6\ \Omega$	-	5	-	ns
Rise time	$t_r$		-	4	-	
Turn-off delay time	$t_{d(off)}$		-	10	-	
Fall time	$t_f$		-	3	-	

**Gate Charge Characteristics<sup>4)</sup>**

Gate to source charge	$Q_{gs}$	$V_{DD}=100\text{ V}, I_D=7.6\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	3.1	-	nC
Gate to drain charge	$Q_{gd}$		-	1.3	-	
Switching charge	$Q_{sw}$		-	2.4	-	
Gate charge total	$Q_g$		-	9	11.6	
Gate plateau voltage	$V_{plateau}$		-	4.5	-	V
Output charge	$Q_{oss}$	$V_{DD}=100\text{ V}, V_{GS}=0\text{ V}$	-	20	26	nC

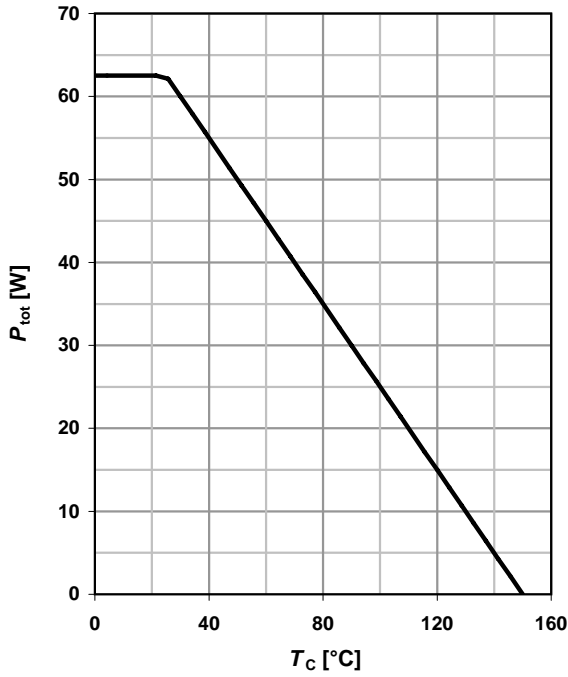
**Reverse Diode**

Diode continuous forward current	$I_S$	$T_C=25\text{ }^\circ\text{C}$	-	-	15.2	A
Diode pulse current	$I_{S,pulse}$		-	-	61	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=15.2\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	1	1.2	V
Reverse recovery time	$t_{rr}$	$V_R=100\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	86	-	ns
Reverse recovery charge	$Q_{rr}$		-	309	-	nC

<sup>4)</sup> See figure 16 for gate charge parameter definition

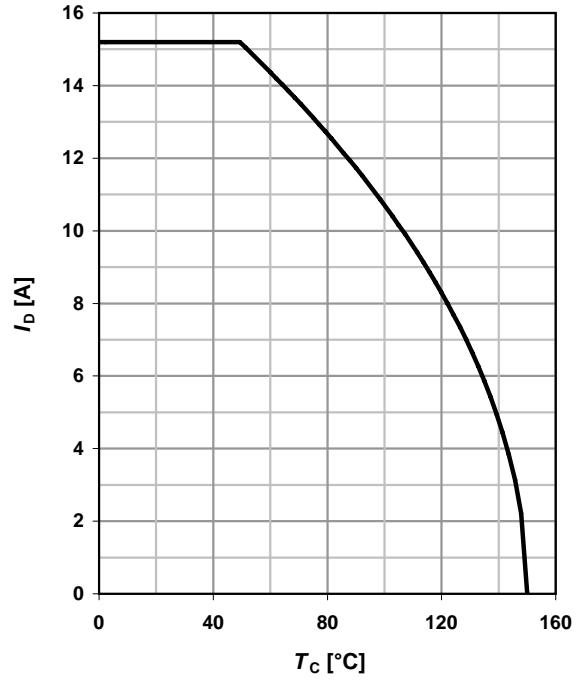
**1 Power dissipation**

$$P_{\text{tot}} = f(T_C)$$



**2 Drain current**

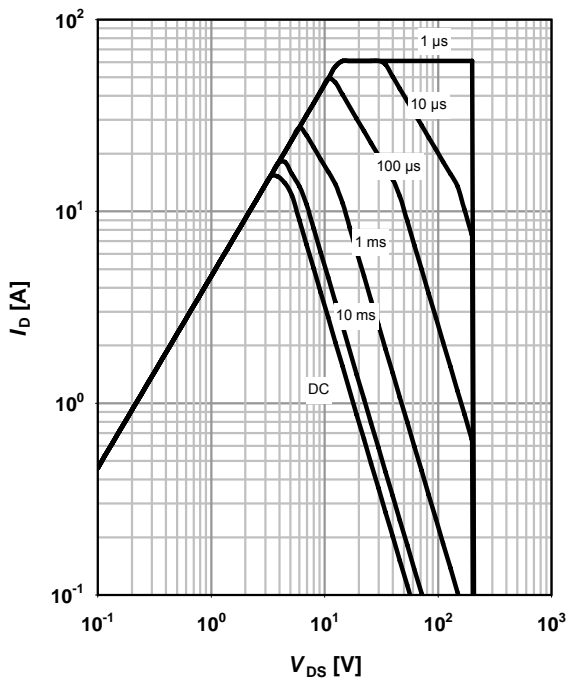
$$I_D = f(T_C); V_{GS} \geq 10 \text{ V}$$



**3 Safe operating area**

$$I_D = f(V_{DS}); T_C = 25 \text{ °C}; D = 0$$

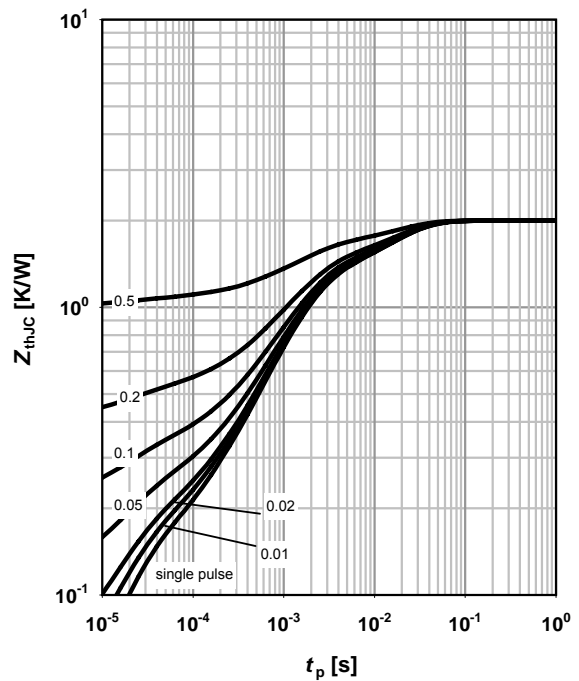
parameter:  $t_p$



**4 Max. transient thermal impedance**

$$Z_{\text{thJC}} = f(t_p)$$

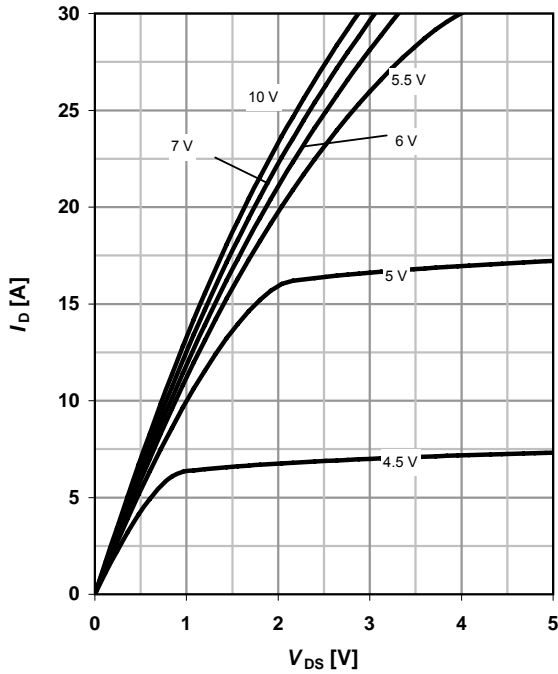
parameter:  $D = t_p / T$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$

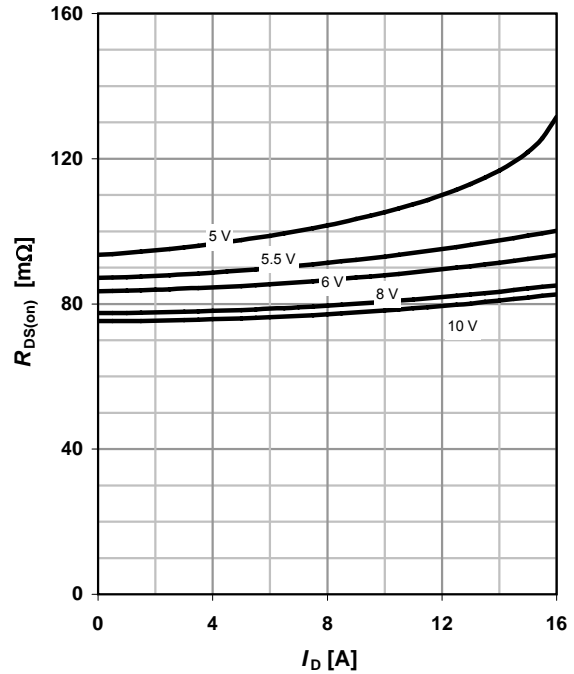
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$

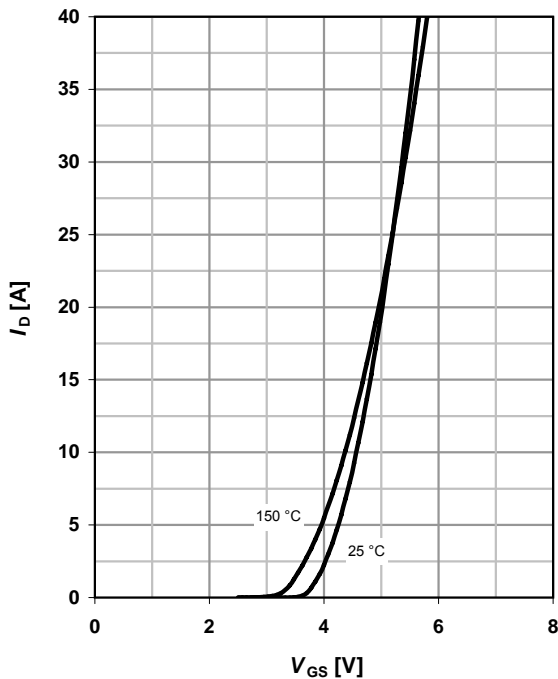
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

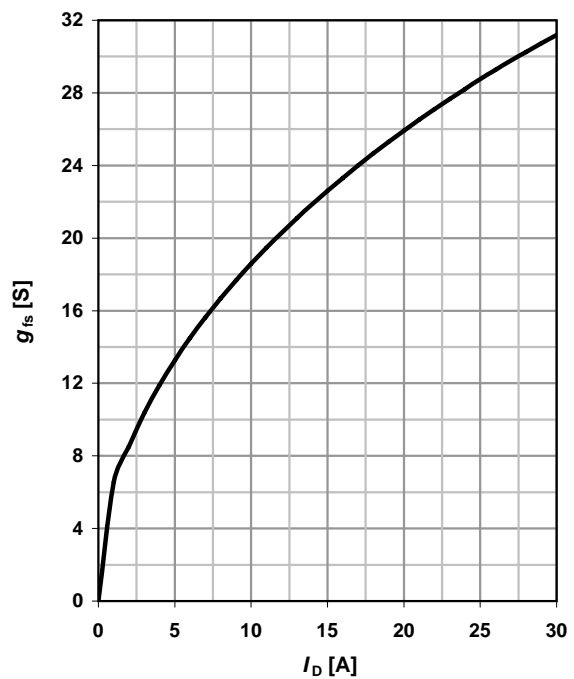
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter:  $T_j$



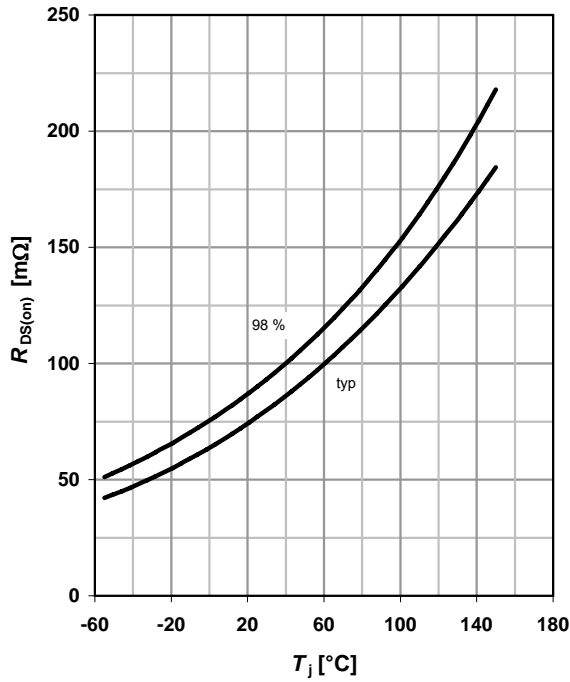
**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25\text{ }^\circ\text{C}$



**9 Drain-source on-state resistance**

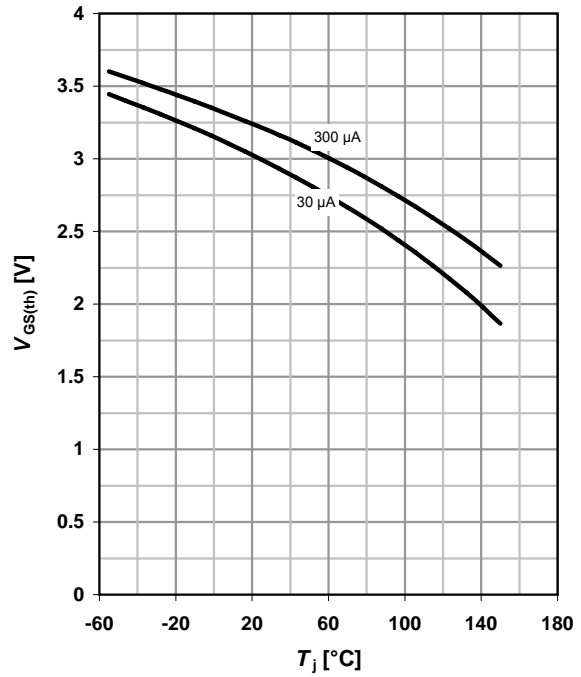
$$R_{DS(on)} = f(T_j); I_D = 7.6 \text{ A}; V_{GS} = 10 \text{ V}$$



**10 Typ. gate threshold voltage**

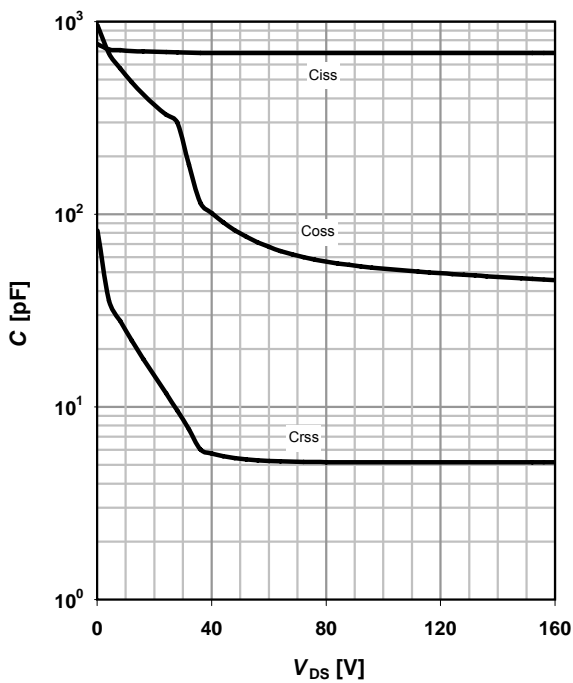
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$

parameter:  $I_D$



**11 Typ. capacitances**

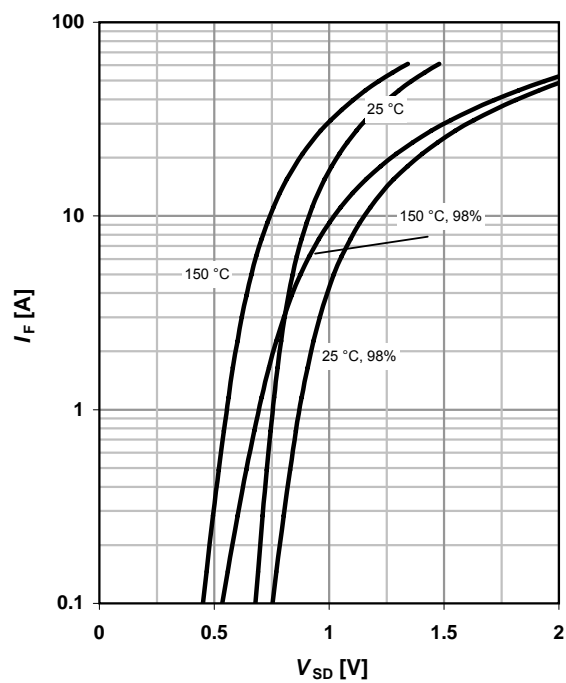
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$



**12 Forward characteristics of reverse diode**

$$I_F = f(V_{SD})$$

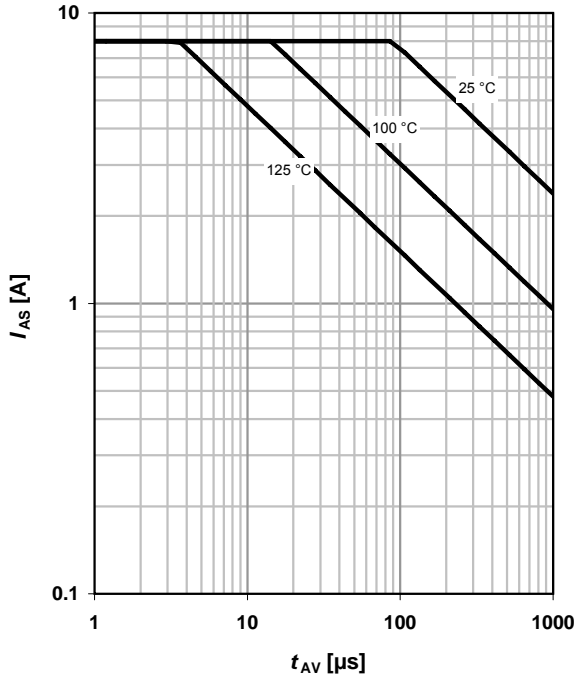
parameter:  $T_j$



**13 Avalanche characteristics**

$I_{AS}=f(t_{AV}); R_{GS}=25\ \Omega$

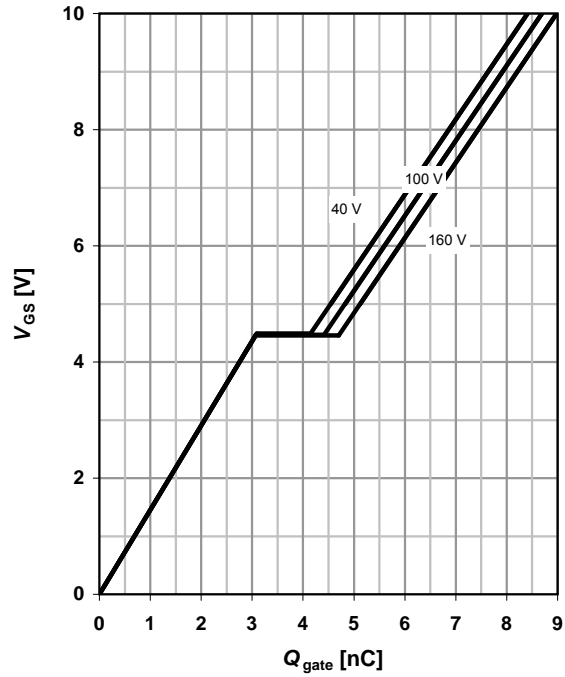
parameter:  $T_{j(start)}$



**14 Typ. gate charge**

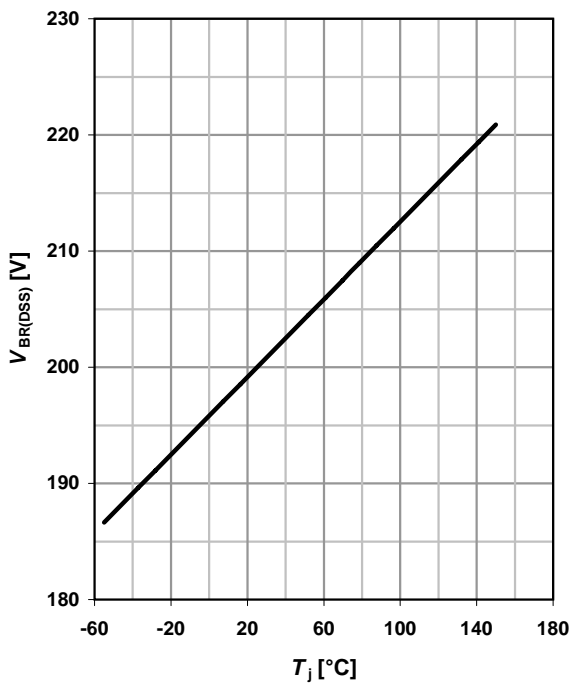
$V_{GS}=f(Q_{gate}); I_D=7.6\ A\ pulsed$

parameter:  $V_{DD}$

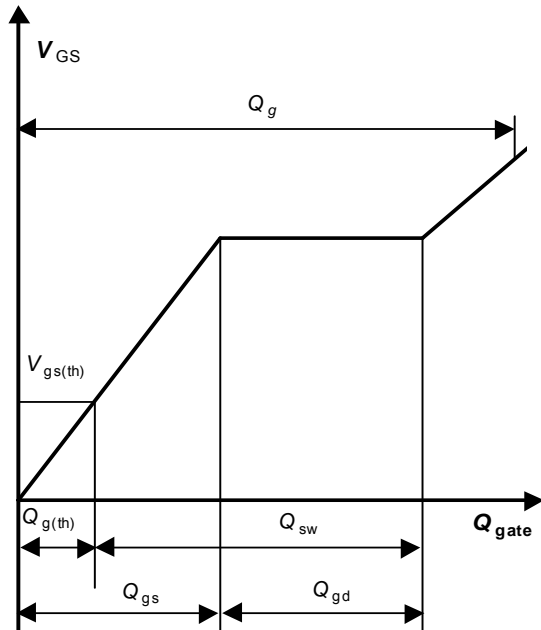


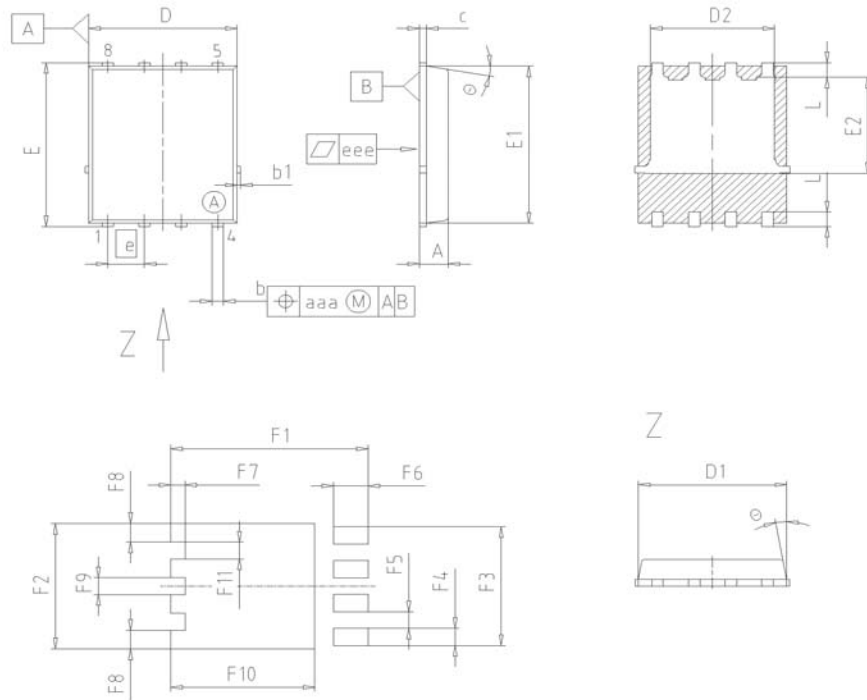
**15 Drain-source breakdown voltage**

$V_{BR(DSS)}=f(T_j); I_D=1\ mA$



**16 Gate charge waveforms**



**Package Outline:PG-TDSON-8**


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.10	0.035	0.043
b	0.34	0.54	0.013	0.021
b1	0.02	0.22	0.001	0.008
c	0.15	0.35	0.006	0.014
D=D1	4.95	5.35	0.195	0.211
D2	4.20	4.40	0.165	0.173
E	5.95	6.35	0.234	0.250
E1	5.70	6.10	0.224	0.240
E2	3.40	3.80	0.134	0.150
e	1.27		0.050	
N	8		8	
L	0.45	0.65	0.018	0.026
□	8.5°		8.5°	
aaa	0.25		0.010	
eee	0.05		0.002	
F1	6.75	6.95	0.266	0.274
F2	4.60	4.80	0.181	0.189
F3	4.36	4.56	0.172	0.180
F4	0.55	0.75	0.022	0.030
F5	0.52	0.72	0.020	0.028
F6	1.10	1.30	0.043	0.051
F7	0.40	0.60	0.016	0.024
F8	0.60	0.80	0.024	0.031
F9	0.53	0.73	0.021	0.029
F10	4.90	5.10	0.193	0.201
F11	0.53	0.73	0.021	0.029

<b>DOCUMENT NO.</b> Z8B00003332
<b>SCALE</b> 
<b>EUROPEAN PROJECTION</b> 
<b>ISSUE DATE</b> 08-03-2007
<b>REVISION</b> 03



**Published by**  
**Infineon Technologies AG**  
**81726 Munich, Germany**  
**© 2010 Infineon Technologies AG**  
**All Rights Reserved.**

**Legal Disclaimer**

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

**Information**

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office ([www.infineon.com](http://www.infineon.com)).

**Warnings**

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain

单击下面可查看定价，库存，交付和生命周期等信息

[>>Infineon Technologies\(英飞凌\)](#)